

# **Description**

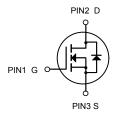
The 5N10-HXY uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



#### **General Features**

 $V_{DS} = 100V I_{D} = 5A$ 

 $R_{DS(ON)} < 125 m\Omega$  @  $V_{GS} = 10V$ 



## **Application**

N-Channel MOSFET **Battery protection** 

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
5N10-HXY	SOT-23	MA6	3000

Absolute Maximum Ratings (T<sub>c</sub>=25<sup>°</sup>Cunless otherwise noted)

Symbol	Parameter	Rating	Units	
VDS	Drain-Source Voltage	100	V	
Vgs	Gate-Source Voltage			
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>			
I <sub>D</sub> @T <sub>A</sub> =70°C	D@T <sub>A</sub> =70°C Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup> 3.2  IDM Pulsed Drain Current <sup>2</sup> 16		А	
Ірм			А	
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	·		
Тѕтс	Storage Temperature Range			
TJ	Operating Junction Temperature Range	-55 to 150	℃	
Reja	Thermal Resistance Junction-ambient(steady state) <sup>1</sup>	nnce Junction-ambient(steady state) <sup>1</sup> 100		
R <sub>θ</sub> JA	R <sub>θJA</sub> Thermal Resistance Junction-ambient(t<10s) <sup>1</sup> 40		°C/W	



# Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	100	108		V
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =4A		110	125	mΩ
NDS(ON)		V <sub>GS</sub> =4.5V , I <sub>D</sub> =2A		120	145	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.7	2.5	V
Ipss	Drain-Source Leakage Current	V <sub>DS</sub> =80V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	
IDSS		V <sub>DS</sub> =80V , V <sub>GS</sub> =0V , T <sub>J</sub> =85°C			50	uA
Igss	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V			±100	nA
Rg	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		2.3	4.6	
Qg	Total Gate Charge (10V)			3.57		
Qgs	Gate-Source Charge	V <sub>DS</sub> =30V , V <sub>GS</sub> =10V , I <sub>D</sub> =4A		0.76		nC
Qgd	Gate-Drain Charge			0.71		
Td(on)	Turn-On Delay Time	V <sub>DD</sub> =30V , V <sub>GS</sub> =10V , R <sub>G</sub> =3.3 I <sub>D</sub> =1A		11		
Tr	Rise Time			6		ns ns
Td(off)	Turn-Off Delay Time			30		
T <sub>f</sub>	Fall Time			4		
Ciss	Input Capacitance			182		
Coss	Output Capacitance	V <sub>DS</sub> =50V , V <sub>GS</sub> =0V , f=1MHz		30		pF
Crss	Reverse Transfer Capacitance			3.6		
ls	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			2	Α
VsD	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C			1.2	V

<sup>1.</sup> The data tested by surface mounted on a 1 inch $^2\,\text{FR-4}$  board with 2OZ copper.

<sup>2.</sup>The data tested by pulsed , pulse width  $\leq 300 us$  , duty cycle  $\leq 2\%$  3.The power dissipation is limited by 150°C junction temperature

<sup>4.</sup> The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



# **Typical Characteristics**

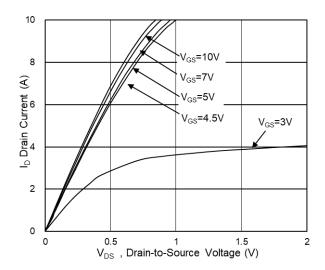


Fig.1 Typical Output Characteristics

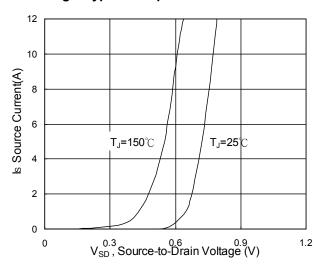


Fig.3 Source Drain Forward Characteristics

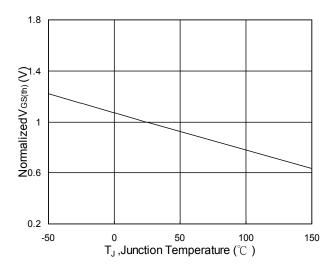


Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$ 

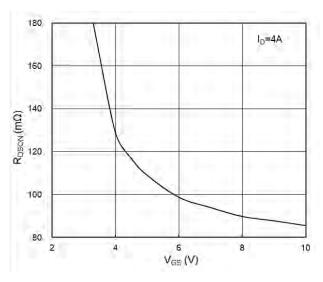


Fig.2 On-Resistance vs G-S Voltage

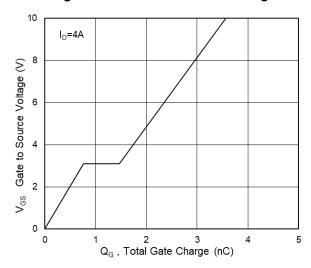


Fig.4 Gate-Charge Characteristics

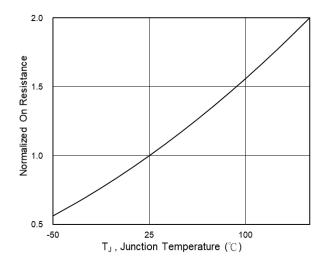
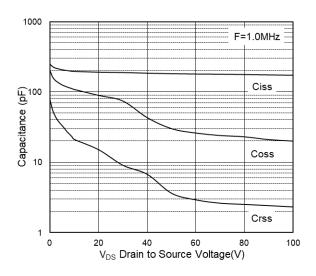


Fig.6 Normalized R<sub>DSON</sub> vs T<sub>J</sub>





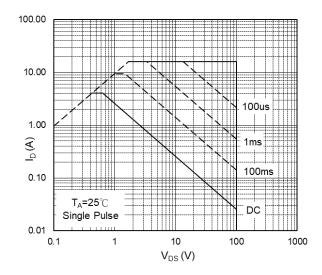


Fig.7 Capacitance

Fig.8 Safe Operating Area

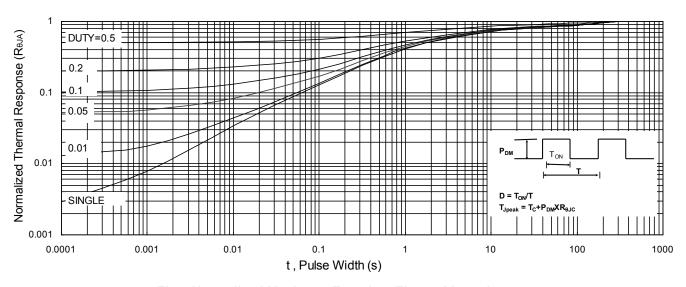


Fig.9 Normalized Maximum Transient Thermal Impedance

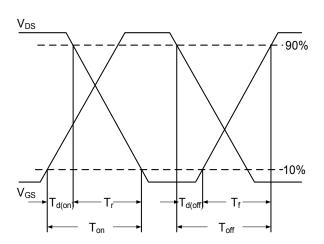


Fig.10 Switching Time Waveform

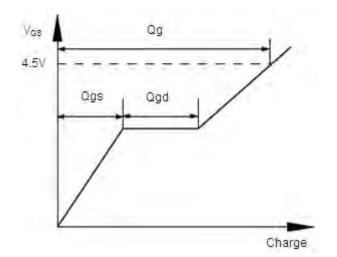
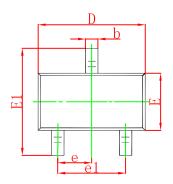
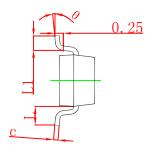


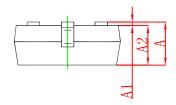
Fig.11 Gate Charge Waveform



# **SOT-23 Package Outline Dimensions**

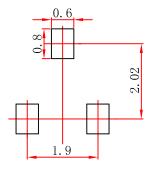






Cumphal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



# Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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